

### LESD8D5.0AT5G ESD PROTECTION DIODE

#### **Discription**

The LESD8D5.0AT5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

### **Applications**

- I Cellular phones audio
- I MP3 players
- I Digital cameras
- I Portable applicationss
- I mobile telephone

#### **Features**

- Low Leakage
- I Response Time is Typically < 1 ns
- I ESD Rating of Class 3 (> 16 kV) per Human Body Model
- I IEC61000-4-2 Level 4 ESD Protection
- I These are Pb-Free Devices
- We declare that the material of product compliance with RoHS requirements.

# LESD8D5.0AT5G





#### **Ordering information**

Device	Marking	Shipping
LESD8D5.0AT5G	GA	10000/Tape&Reel

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		±15 ±8	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1) @ $T_A=25^{\circ}C$	PD	200	mW
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	$^{\circ}$
Lead Solder Temperature – Maximum (10	TL	260	${\mathbb C}$
Second Duration)			

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0\*0.75\*0.62 in.

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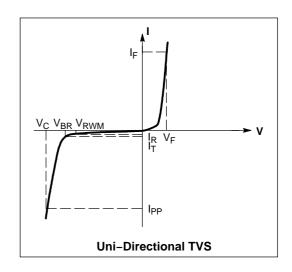


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#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
$V_{RWM}$	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
P <sub>pk</sub>	Peak Power Dissipation
С	Capacitance @ V <sub>R</sub> = 0 and f = 1.0 MHz



#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

	$V_{RWM}$	I <sub>R</sub>	$V_{BR}$	I <sub>T</sub>	I <sub>PP</sub>	Vc	P <sub>PK</sub>	С
	(V)	( µ A)	(V)	(mA)	(A)	(V)	(W)	(pF)
Device		@	@ I <sub>T</sub>			@ Max I <sub>PP</sub>	(8*20 µs)	
		$V_{RWM}$	(Note 2)		(Note 3)	(Note 3)		
	Max	Max	Min		Max	Max	Тур	Тур
LESD8D5.0AT5G	5.0	1.0	6.2	1.0	6	11	66	30

- 2.  $V_{BR}$  is measured with a pulse test current IT at an ambient temperature of 25  $^{\circ}{\!\!\!^{\circ}}{\!\!\!^{\circ}}$
- 3. Surge current waveform per Figure 3.

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#### TYPICAL CHARACTERISTICS

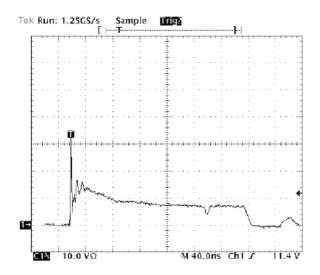


Figure 1. Positive 8kV contact per IEC 61000-4-2-LESD11D5.0T5G

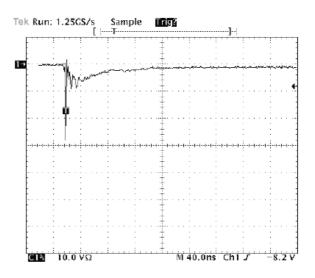


Fig 2. Negative 8kV contact per IEC 61000-4-2-LESD11D5.0T5G

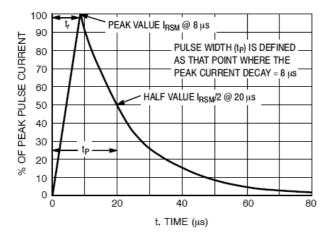


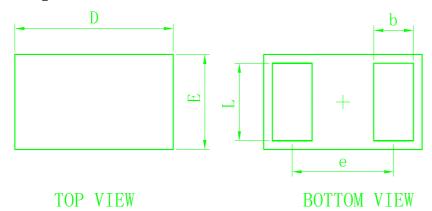
Figure 3. 8\*20 µs Pulse Waveform

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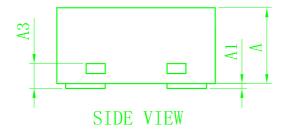


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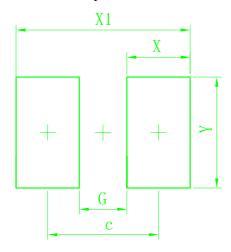
## Package Outline Dimension



S0D882				
Dim	Min	Тур	Max	
D	0.95	1.00	1.05	
Е	0. 55	0.60	0.65	
е	_	0.64	-	
L	0.44	0.49	0.54	
b	0. 20	0. 25	0.30	
A	0.43	0.48	0. 53	
A1	0	-	0.05	
A3	0. 127REF.			
All Dimensions in mm				



## Suggested Pad layout



Dimensions	(mm)
С	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70

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